

描述 / Descriptions

TO-3P 塑封封装 肖特基二极管。

Schottky Barrier Diode in a TO-3P Plastic Package.

特征 / Features

低正向压降，低功耗损失，效率高。

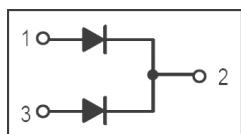
Low forward voltage drop, low power losses, High efficiency operation.

用途 / Applications

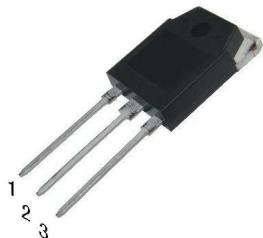
用于高频率逆变器，开关电源，续流二极管，OR-ing 二极管，DC-DC 转换器和电池反向保护。

For use in high frequency inverters, switching power supplies, freewheeling diodes, OR-ing diode, dc-to-dc converters and reverse battery protection.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



PIN1: Anode PIN 2: Cathode PIN 3: Anode

放大及印章代码 / h_{FE} Classifications & Marking

见印章说明。 See Marking Instructions.

极限参数 / Absolute Maximum Ratings(Ta=25°C)

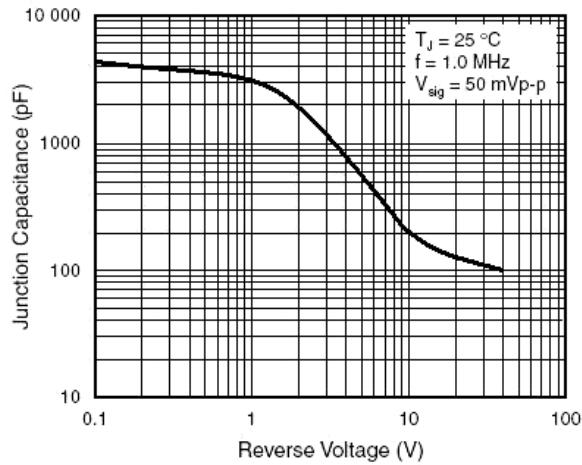
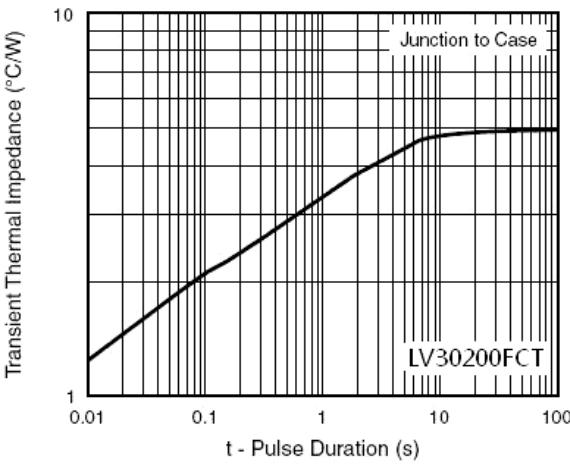
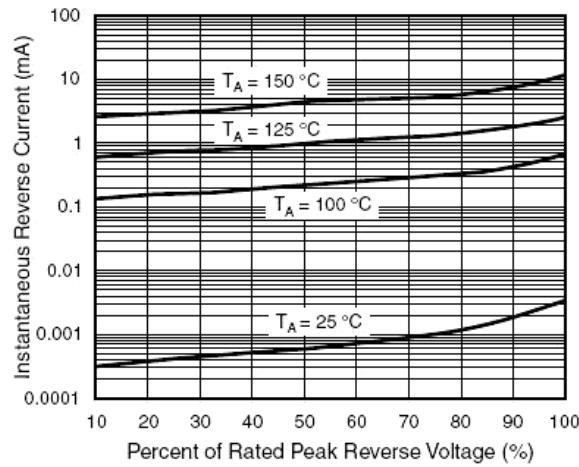
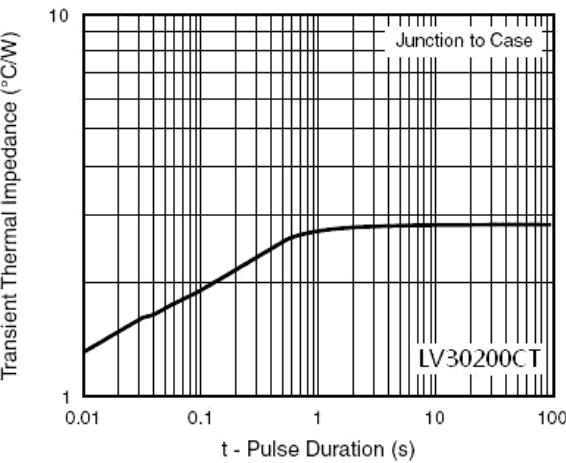
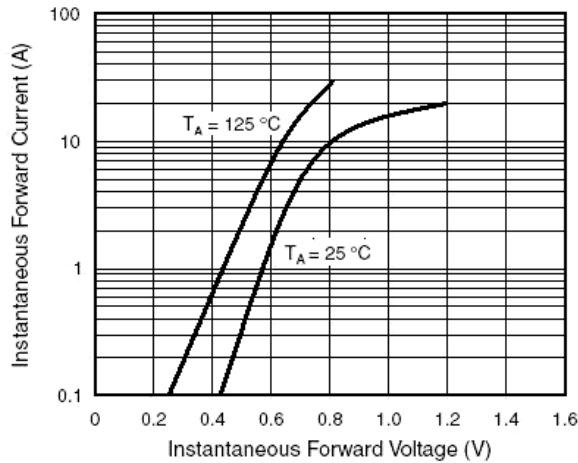
参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Peak Repetitive Reverse Voltage	V_{RM}		
Working Peak Reverse Voltage	V_{RWM}	200	V
DC Blocking Voltage	V_{DC}		
RMS Reverse Voltage	V_{RMS}	140	V
Average forward current	$I_{F(AV)}$	2×15	A
Non-Repetitive Peak Forward Surge Current	I_{FSM}	200	A
Thermal Resistance Junction to Ambient case	$R_{\theta Jc}$	1.4	°C/W
Operating and Storage Temperature Range	$T_j - T_{stg}$	-40~+150	°C

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Reverse Breakdown Voltage	V_{BR}	$I_R = 1\text{mA}(Ta=25^\circ\text{C})$	200			V
Forward Voltage	V_F	$I_F = 5\text{A}(Ta=25^\circ\text{C})$		0.73	0.85	V
		$I_F = 10\text{A}(Ta=25^\circ\text{C})$		0.80	0.95	V
		$I_F = 15\text{A}(Ta=25^\circ\text{C})$		0.92	1.15	V
		$I_F = 5\text{A}(Ta=125^\circ\text{C})$		0.58		V
		$I_F = 10\text{A}(Ta=125^\circ\text{C})$		0.66		V
		$I_F = 15\text{A}(Ta=125^\circ\text{C})$		0.71	0.85	V
Instantaneous Reverse current (Note 1)	I_R (Note 1)	$V_R = 200\text{V}(Ta=25^\circ\text{C})$		4	20	μA
		$V_R = 200\text{V}(Ta=125^\circ\text{C})$		5	10	mA

注/Notes:

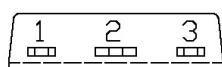
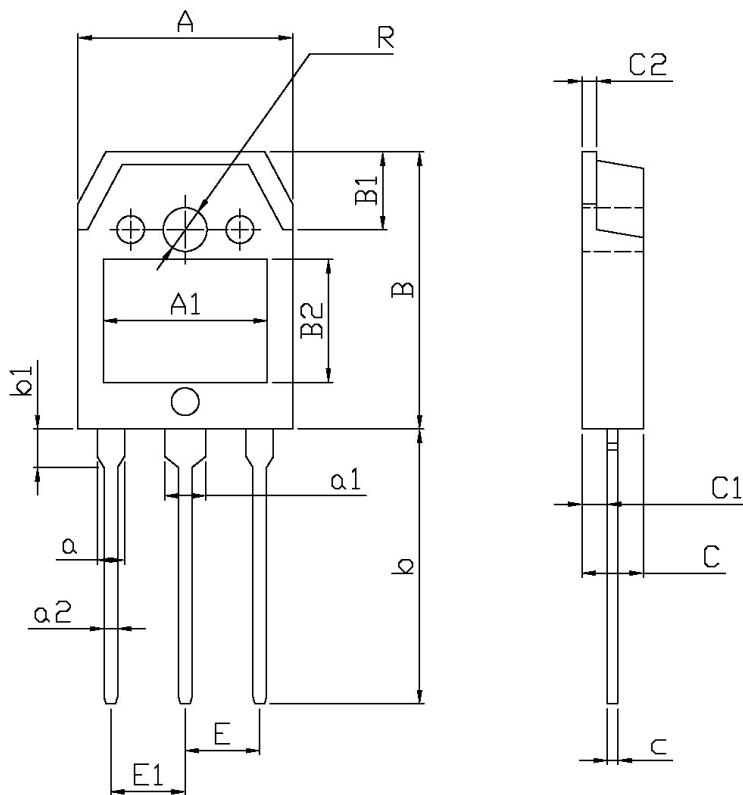
- 使用极短的测试时间，以尽量减少自热效应。/Short duration pulse test used to minimize self-heating effect.
- 除非特别注明，数值为一个芯片的参数。/ Unless otherwise noted, values for the parameters of a single chip.

电参数曲线图 / Electrical Characteristic Curve


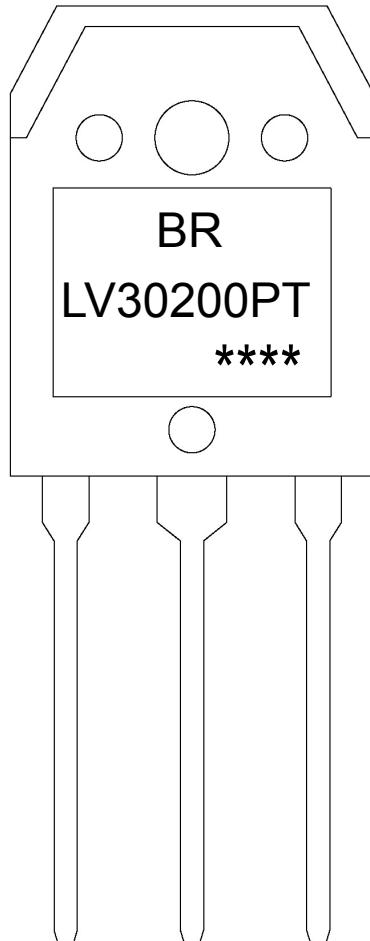
外形尺寸图 / Package Dimensions

T□-3P

单位: mm



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	15.4	16.0	alpha2	0.8	1.2
R	3.1	3.5	E	5.45	
B	19.8	20.8	E1	5.45	
B1	5.5	5.9	C	4.3	4.7
B2	9.0		C1	1.2	1.6
A1	12.0		C2	1.4	1.6
b	19.6	20.6	c	0.5	0.7
b1	3.0	3.4			
alpha	1.8	2.2			
alpha1	2.8	3.2			

印章说明 / Marking Instructions**说明：**

BR : 为公司代码

LV30200PT : 为产品型号

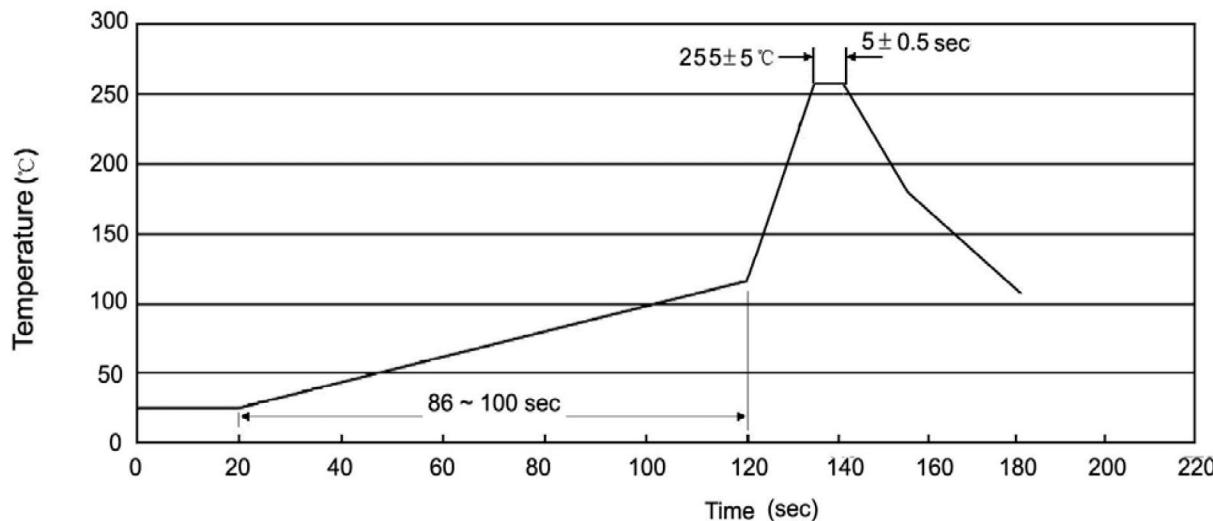
**** : 为生产批号代码，随生产批号变化。

Note:

BR: Company Code.

LV30200PT: Product Type.

****: Lot No. Code, code change with Lot No.

波峰焊温度曲线图(无铅) / Temperature Profile for Dip Soldering(Pb-Free)

说明：

- 1、预热温度 25~150°C , 时间 60~90sec;
- 2、峰值温度 255±5°C , 时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:25~150°C, Time:60~90sec.
- 2.Peak Temp.:255±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度 : 270±5°C

时间 : 10±1 sec.

Temp.:270±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.
套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-3P	30	15	450	5	2250	497.5×46×8	555×164×50	575×290×180

使用说明 / Notices